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The HD74LS283 adder is electrically and functionally identical to the HD74LS83A, respectively; only the arrangement of the terminals has been changed.

This improved full adder performs the addition of two 4-bit binary words.

The sum  $(\Sigma)$  outputs are provided for each bit and the resultant carry  $(C_4)$  is obtained from the fourth bit. This adder features full internal look-ahead across all four bits generating the carry term in then nanoseconds.

The adder logic, including the carry, is implemented in its true form.

End arround carry can be accomplished without the need for logic or level inversion.

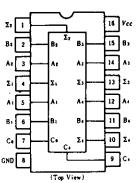
#### FUNCTION TABLE

			-	Outputs							
	Inp	uts		When Co™L		When C2-L	When C₀-H		When C <sub>2</sub> =H		
A <sub>1</sub> /	B <sub>1</sub>	A2/	Bı	$\Sigma_1$	Σ2/	C <sub>2</sub> /	Σι/	$\Sigma_1$	C <sub>2</sub> /		
/ As	∕B₃	/A.	∕B₁	<b>Σ</b> 3	/ Σ,	∕ C₁	$\sum_{1}$	/ Σι	∕ C,		
L	L	L	L	L	L	L	Н	L	L		
H	L	L	L	Н	L_	L	L	Н	L		
L	н	L	L	H	L	L	L	H	L		
Н	Н	L	L	I.	Н	L	Н	Н	L		
L	L	н	L	1.	Н	L	Н	Н	L		
Н	L.	Н	L	Н	Н	L	L	L_	Н		
L	Н	Н	L	H	Н	L	L	L	Н		
Н	Н	Н	L	I.	L	Н	Н	L	Н		
L	L	L	н	J.	Н	L	Н	Н	L		
Н	L	L	Н	Н	Н	L	L	L	Н		
L	Н	L	Н	Н	Н	L	L	L	Н		
H	Н	L	Н	I.	L	Н	Н	L	Н		
L	L	Н	Н	1.	L	Н	Н	L	Н		
Н	L	Н	Н	Н	L	Н	L	Н	Н		
L	Н	Н	Н	Н	L	Н	L	Н	Н		
Н	Н	Н	Н	I.	Н	Н	Н	Н	Н		

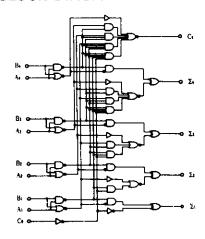
H; high level, L; low level

Notes) Input conditions at  $A_1$ ,  $B_1$ ,  $A_2$ ,  $B_2$ , and  $C_0$  are use to determine outputs  $E_1$  and  $E_2$  and the value of the internal carry  $C_2$ . The values at  $C_2$ ,  $A_3$ ,  $B_3$ ,  $A_4$ , and  $B_4$  are then used to determine outputs  $E_3$ ,  $E_4$ , and  $C_4$ .

#### **PIN ARRANGEMENT**



#### **■BLOCK DIAGRAM**



# **ELECTRICAL CHARACTERISTICS** $(Ta = -20 \sim +75^{\circ}C)$

Iı	tem	Symbol	Test Conditions			min	typ*	max	Unit
Input voltage		ViH				2.0	-	_	V
		V <sub>IL</sub>					_	0.8	V
Output voltage		V <sub>aH</sub>	$V_{CC}=4.75$ V, $V_{I}$	2.7		_	V		
		1,,	$V_{CC} = 4.75 \text{ V},  V_{IH} = 2 \text{ V},  V_{IL} = 0.8 \text{ V}$ $I_{OL} = 8 \text{ mA}$				-	0.4	v
		V <sub>01</sub>				_		0.5	
	except Co	,	Vcc -5.25V, V1-2.7V				_	40	μΑ
	C <sub>0</sub>	11H				_		20	
	except C₀		V			_		-0.8	mA
Input current	C <sub>0</sub>	In	$V_{cc} = 5.25 \text{V}, V_t$	_	_	-0.4			
	except Co	ļ	V <sub>cc</sub> -5.25V, V <sub>i</sub> -7V				_	0.2	mA
	Св	I,				_		0.1	
Short-circuit o	output current	Ios	V <sub>cc</sub> = 5.25V			20		-100	mA
Supply current			V <sub>cc</sub> =5.25V	All inputs grounded			22	39	
		Ice.		All B low, other	All B low, other inputs at 4.5V			34	mA
			All inputs at 4.5V		5 V	-	19	34	l
Input clamp vo	ltage	Vik	$V_{cc} = 4.75 \text{V}, I_{IN} = -18 \text{mA}$			_	-	-1.5	V

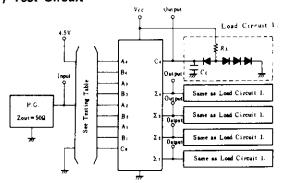
<sup>\*</sup> VCC=5V, Ta=25°C

## **ESWITCHING CHARACTERISTICS** ( $V_{cc} = 5V$ , $T_a = 25^{\circ}C$ )

Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
	t <sub>PLH</sub>	6	Σi		-	16	24	ns
	t <sub>PHL</sub>	C <sub>0</sub>				15	24	ns
	t <sub>PLH</sub>	Ai, Bi	Σi	$C_{\epsilon}=15 \text{pF}, R_{L}=2 \text{k}\Omega$	_	15	24	ns
	t <sub>PHL</sub>					15	24	ns
Propagation delay time	t <sub>PLH</sub>	C <sub>0</sub>	C,		_	11	17	ns
	₽ <sub>PHL</sub>				_	11	22	ns
	t <sub>PLH</sub>	Ai, Bi	C <sub>4</sub>			11	17	r.s
	t <sub>PHL</sub>				_	12	17	ns

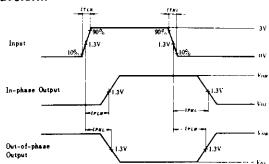
#### **TESTING METHOD**

#### 1) Test Circuit



Notes) 1.  $C_L$  includes probe and jig capacitance. 2. All diodes are 1S2074  $\textcircled{\mathbb{H}}$ ,

#### Waveform



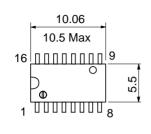
Input pulse;  $t_{TLH} \le 15$ ns,  $t_{THL} \le 6$ ns, PRR = 1MHz, duty cycle 50%.

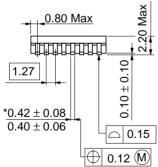
## 2) Testing Table

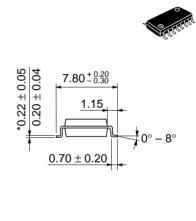
		Inputs								Outputs					
Item	From input to output	В4	A <sub>4</sub>	В	A3	Bı	A2	Βι	Aι	C₀	C۱	Σι	Σι	Σ2	Σι
		GND	GND	GND	GND	GND	GND	GND	GND	IN	_	_	_	_	OUT
	Co→Σi or C.	GND	4.5V	GND	4.5V	GND	4.5V	GND	4.5V	IN	OUT	OUT	OUT	OUT	อบา
				GND	GND	GND	CNIE	GND IN	IN	CND				_	OUT
		GND	GND				GND		GND	GND					00
		GND GNI	CNID	D CND	GND	GND	IN GND GND	GND	GND		_	l _	OUT	l _	
t plh			GND	GND		IN		GND	GND	<u> </u>				L	<u> </u>
		GND	GND	GND	IN	GND	GND	GND	GND	GND	_	_	OUT	_	
		GND	GND	IN	GND	0110	02	0.112		L	<del>                                     </del>	<u> </u>	<u> </u>	ļ	L
₿ PHL		GND	IN	GND	GND GND	GND	GND	GND	GND	GND	_	OUT	-	_	
• ****	Ai or Bi  →Σi or C <sub>4</sub>	IN	GND	0									<del> </del>		
		GND	GND	GND	GND	GND	GND -	4.5V	IN	GND	_	_		OUT	OUT
			J				L	IN	4.5V	ļ		<b></b>	<del> </del> -		
		GND	GND	ND GND	GND	<u> </u>	4.5V IN	GND	GND	GND		–	OUT	OUT	
	1					IN	4.5V	<del> </del>	ļ	<del> </del>		<b>_</b>			$\vdash$
		GND	GND	4.5V	IN	GND GND	GND	GND	GND	_	OUT	OUT		-	
		<b></b>		IN	4.5V			L	<b></b>	<del> </del>		<b></b>	<del> </del> -	<b>├</b> ──	-
		4.5V	IN	GND	GND	GND	GND	GND	GND	GND	OUT	OUT			
		IN	4.5V		0112		l			<u> </u>	<u> </u>		<u> </u>	L	<u> </u>

Unit: mm 19.20 20.00 Max 16 7.40 Max 6.30 1.3 1.11 Max 7.62 5.06 Max 2.54 Min 0.51 Min  $0.25^{+0.13}_{-0.05}$  $0.48 \pm 0.10$  $2.54\pm0.25$  $0^{\circ} - 15^{\circ}$ Hitachi Code DP-16 **JEDEC** Conforms EIAJ Conforms Weight (reference value) 1.07 g

Unit: mm



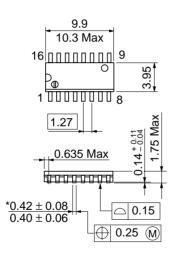


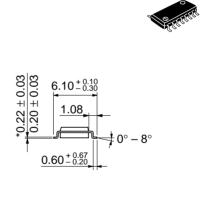


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.24 g

Unit: mm





\*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

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